

# Tokio Takahashi

## List of Publications by Year in descending order

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28  
papers

305  
citations

933447

10  
h-index

888059

17  
g-index

28  
all docs

28  
docs citations

28  
times ranked

343  
citing authors

#	ARTICLE	IF	CITATIONS
1	Growth and Characterization of GaN/AlN Resonant Tunneling Diodes for High-Performance Nonvolatile Memory. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021, 218, 2000495.	1.8	1
2	High-quality nanodisk of InGaN/GaN MQWs fabricated by neutral-beam-etching and GaN regrowth: towards directional micro-LED in top-down structure. <i>Semiconductor Science and Technology</i> , 2020, 35, 075001.	2.0	13
3	Near-Complete Elimination of Size-Dependent Efficiency Decrease in GaN Micro-Light-Emitting Diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1900380.	1.8	33
4	Switching characteristics of nonvolatile memory using GaN/AlN resonant tunneling diodes. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 091001.	1.5	3
5	Near-Complete Elimination of Size-Dependent Efficiency Decrease in GaN Micro-Light-Emitting Diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1970075.	1.8	4
6	Impact of substrate off-angle on the $m$ -plane GaN Schottky diodes. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 04FG01.	1.5	14
7	Impact of strain state on the ultrathin AlN/GaN superlattice growth on Si(110) substrates by metalorganic chemical vapor deposition. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 010306.	1.5	2
8	High thermal stability of abrupt $\text{SiO}_2$ /GaN interface with low interface state density. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 04FG11.	1.5	14
9	Comparison of Electrical Properties of Ni/n-GaN Schottky Diodes on $c$ -plane and $m$ -plane GaN Substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1700362.	1.8	9
10	Stabilization of nonvolatile memory operations using GaN/AlN resonant tunneling diodes by reducing structural inhomogeneity. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 070310.	1.5	6
11	High quality thin AlN epilayers grown on Si(110) substrates by metal-organic chemical vapor deposition. <i>CrystEngComm</i> , 2017, 19, 1204-1209.	2.6	12
12	Electrical properties of Ni/n-GaN Schottky diodes on freestanding $m$ -plane GaN substrates. <i>Applied Physics Express</i> , 2017, 10, 041001.	2.4	15
13	Nitrogen vacancies as a common element of the green luminescence and nonradiative recombination centers in Mg-implanted GaN layers formed on a GaN substrate. <i>Applied Physics Express</i> , 2017, 10, 061002.	2.4	70
14	Resistance switching memory operation using the bistability in current-voltage characteristics of GaN/AlN resonant tunneling diodes. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 100301.	1.5	9
15	Effect of double superlattice interlayers on growth of thick GaN epilayers on Si(110) substrates by metalorganic chemical vapor deposition. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 05FB02.	1.5	3
16	Mechanisms of the micro-crack generation in an ultra-thin AlN/GaN superlattice structure grown on Si(110) substrates by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , 2015, 118, .	2.5	5
17	High-quality GaN film and AlGaIn/GaN HEMT grown on 4-inch Si(110) substrates by MOCVD using an ultra-thin AlN/GaN superlattice interlayer. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 1075-1078.	1.5	8
18	Self-generated microcracks in an ultra-thin AlN/GaN superlattice interlayer and their influences on the GaN epilayer grown on Si(110) substrates by metal-organic chemical vapor deposition. <i>CrystEngComm</i> , 2015, 17, 5014-5018.	2.6	9

#	ARTICLE	IF	CITATIONS
19	Investigating the bistability characteristics of GaN/AlN resonant tunneling diodes for ultrafast nonvolatile memory. Japanese Journal of Applied Physics, 2015, 54, 034201.	1.5	14
20	Enhancement of the evanescent wave coupling effect in a sub-wavelength-sized GaAs/AlGaAs ridge structure by low-refractive-index surface layers. Optics Express, 2014, 22, A1559.	3.4	3
21	Study on AlGaIn/GaN growth on carbonized Si substrate. Japanese Journal of Applied Physics, 2014, 53, 04EH09.	1.5	1
22	Strain states in GaN films grown on Si(111) and Si(110) substrates using a thin AlN/GaN superlattice interlayer. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 473-476.	0.8	4
23	Enhanced light extraction in GaN-based light-emitting diodes by evanescent wave coupling effect. Applied Physics Express, 2014, 7, 102101.	2.4	7
24	Role of an ultra-thin AlN/GaN superlattice interlayer on the strain engineering of GaN films grown on Si(110) and Si(111) substrates by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2013, 103, 231908.	3.3	14
25	Modulation of Strain States in GaN Films by a Thin AlN/GaN Superlattice Interlayer Grown on Si(110) Substrates. Japanese Journal of Applied Physics, 2013, 52, 08JB05.	1.5	8
26	Realization of compressively strained GaN films grown on Si(110) substrates by inserting a thin AlN/GaN superlattice interlayer. Applied Physics Letters, 2012, 101, .	3.3	19
27	Light Source Position Dependence of Evanescent Wave Coupling Effect in Narrow GaAs/AlGaAs Ridge Structure. Japanese Journal of Applied Physics, 2012, 51, 040205.	1.5	1
28	Light Source Position Dependence of Evanescent Wave Coupling Effect in Narrow GaAs/AlGaAs Ridge Structure. Japanese Journal of Applied Physics, 2012, 51, 040205.	1.5	4